

9097250 TOSHIBA (DISCRETE/OPTO)

67C 09264 DT-11-07

Silicon Planar Type

Zener Diode

02BZ2.2 ~ 02BZ4.7

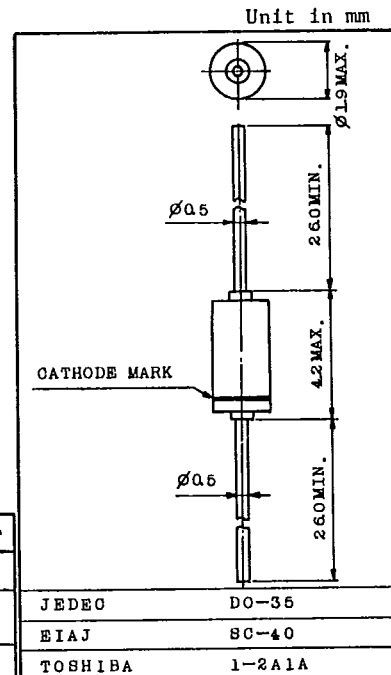
LOW VOLTAGE REGULATION AND LOW REFERENCE
VOLTAGE APPLICATIONS.

FEATURES:

- Low Zener Voltage : $V_Z=2.2\sim 4.7V$ (Typ.)
- Small Zener Impedance : $r_d=28\Omega$ (Max.) (02BZ2.2~3.9)
- Hermetically Sealed Miniature Glass Package
- Fast Reverse Recovery Time ($t_{rr}\approx 10ns$)

MAXIMUM RATINGS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Power Dissipation	P	250	mW
Surge Power Dissipation (Note 1)	P _{SURGE}	1250	mW
Maximum(Peak) Zener Current	I _{ZM}	(Note 2)	mA
Junction Temperature	T _j	175	°C
Storage Temperature Range	T _{stg}	-65~175	°C



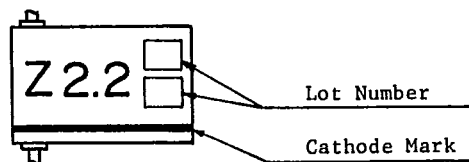
Weight : 0.14g

Note 1 : Allowable peak power for surge pulse of 1 second.

2 : See ELECTRICAL CHARACTERISTICS.

3 : Marking

Example : 02BZ2.2



TOSHIBA CORPORATION

9097250 TOSHIBA (DISCRETE/OPTO)

67C 09265 D T-11-07

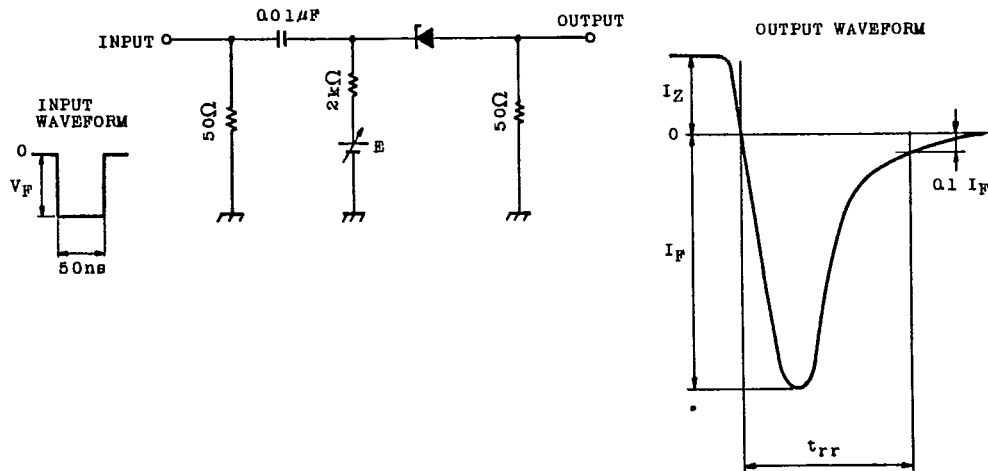
02BZ2.2 ~ 02BZ4.7

ELECTRICAL CHARACTERISTICS (Ta=25°C)

TYPE (Note 2)	ZENER VOLTAGE V _Z (V)			ZENER IMPEDANCE r _d (Note 4) (Ω)		TEMPERATURE COEFFICIENT OF ZENER VOLTAGE r _Z (%/°C)		ZENER CURRENT I _Z (mA)	REVERSE CURRENT I _R (μA) MAX.	REVERSE VOLTAGE V _R (V)	MAXIMUM (PEAK) ZENER CURRENT I _{ZM} (mA) MAX.
	MIN.	TYP.	MAX.	TYP.	MAX.	TYP.	MAX.				
02BZ2.2	1.88	2.2	2.56	15	28	-0.088	-0.100	10	10	1.0	82
02BZ2.7	2.28	2.7	3.20	16	28	-0.078	-0.100	10	5.0	1.0	70
02BZ3.3	2.80	3.3	3.80	18	28	-0.070	-0.090	10	1.0	1.0	60
02BZ3.9	3.40	3.9	4.60	19	28	-0.063	-0.080	10	1.0	1.0	51
02BZ4.7	4.00	4.7	5.40	25	35	-0.055	-0.070	10	1.0	1.0	43

Note 4 : Test frequency : f=1kHz

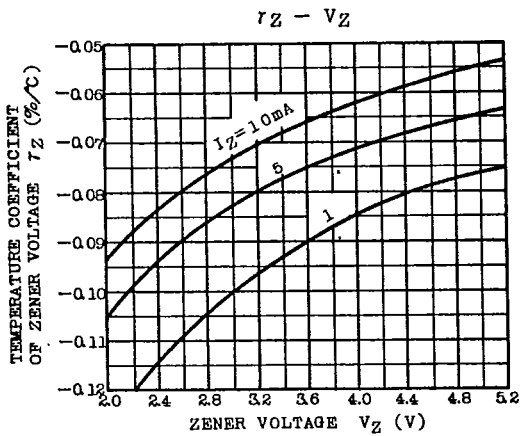
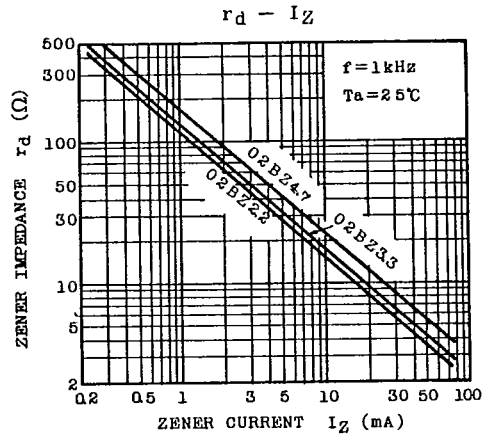
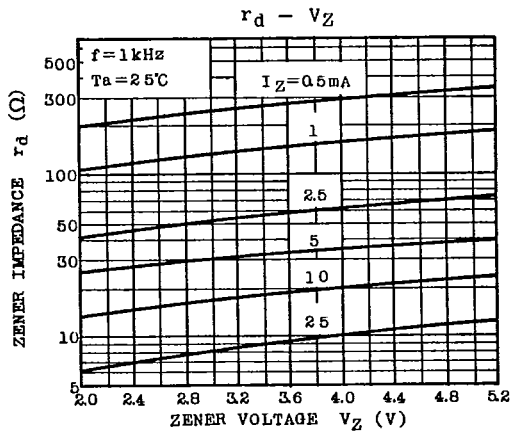
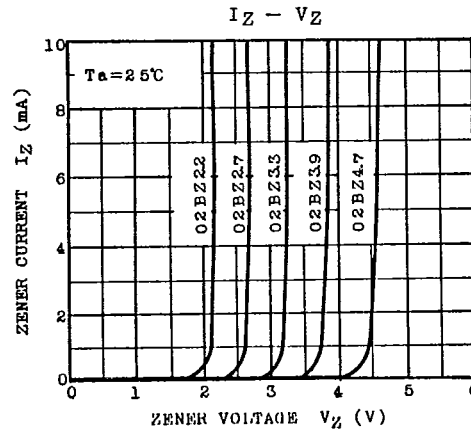
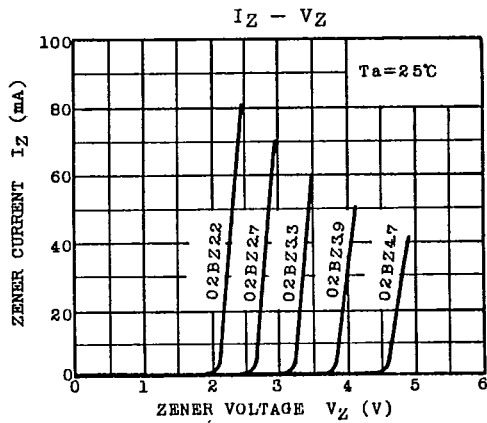
t_{rr} TEST CIRCUIT



9097250 TOSHIBA (DISCRETE/OPTO)

67C 09266 D T-11-07

02BZ2.2 ~ 02BZ4.7



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9097250 TOSHIBA (DISCRETE/OPTO)

67C 09267 DT-11-07

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